

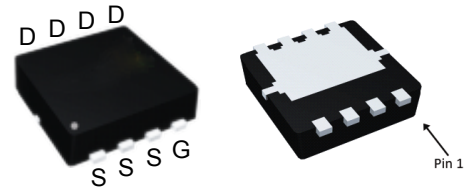
Features

- 100V/15A,
 $R_{DS(ON)} = 60m\Omega$ (typ.) @ $V_{GS} = 10V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)

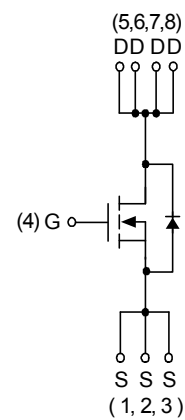
Applications

- Power Management in DC/DC Converter.
- POE Protection Switch.

Pin Description



PDFN3.3*3.3-8L



N-Channel MOSFET

Absolute Maximum Ratings (T_A = 25°C Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		100	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _C =25°C	15	A
I _D	Continuous Drain Current	T _C =25°C	15	A
		T _C =100°C	11.3	
I _{DM} ^a	Pulsed Drain Current	T _C =25°C	45	
P _D	Maximum Power Dissipation	T _C =25°C	25	W
		T _C =100°C	10	
R _{θJC}	Thermal Resistance-Junction to Case		5	°C/W
R _{θJA} ^c	Thermal Resistance-Junction to Ambient	Steady State	80	°C/W
I _{AS} ^b	Avalanche Current, Single pulse	L=0.5mH	8	A
E _{AS} ^b	Avalanche Energy, Single pulse	L=0.5mH	16	mJ

Note a : Pulse width limited by maximum junction temperature.

Note b : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature T_J=25°C).

Note c : Surface Mounted on 1in² pad area.

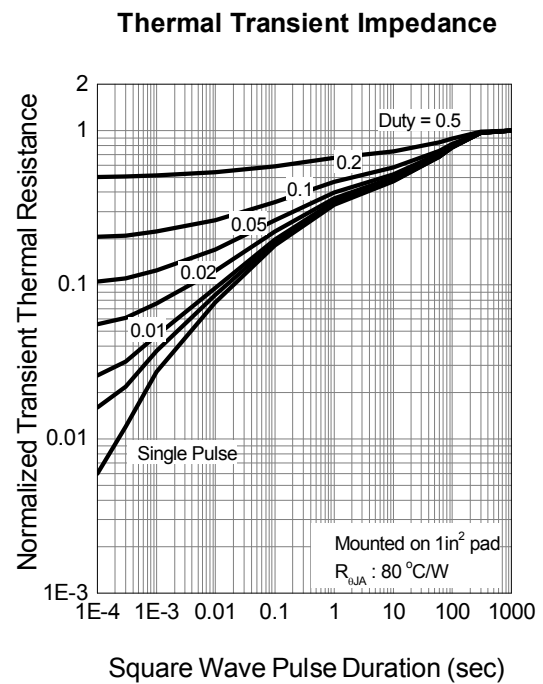
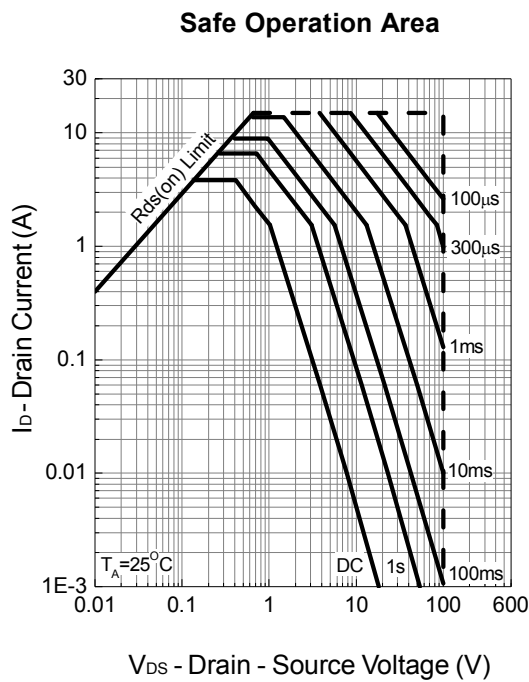
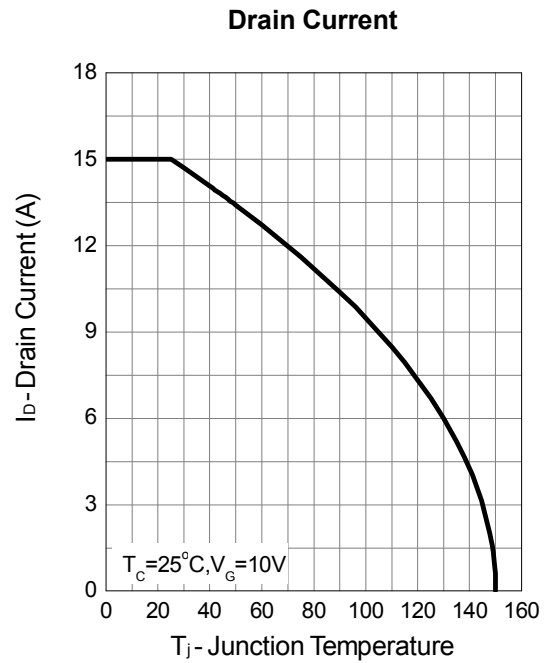
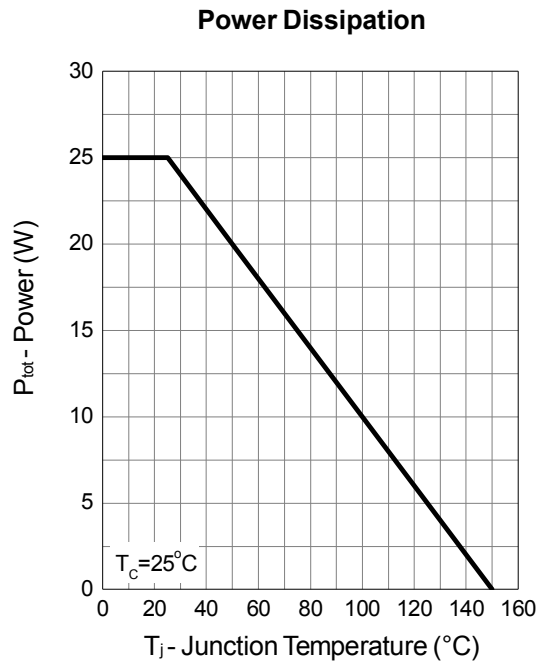
Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =80V, V _{GS} =0V T _J =85°C	-	-	1 30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2	3	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =7A	-	60	75	mΩ
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =7A, V _{GS} =0V	-	0.8	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =7A, dI _{SD} /dt=100A/μs	-	30	-	ns
Q _{rr}	Reverse Recovery Charge		-	40	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	1.5	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, Frequency=1.0MHz	-	160	360	pF
C _{oss}	Output Capacitance		-	103	-	
C _{rss}	Reverse Transfer Capacitance		-	11	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, R _L =30Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	9	17	ns
t _r	Turn-on Rise Time		-	6	11	
t _{d(OFF)}	Turn-off Delay Time		-	14	26	
t _f	Turn-off Fall Time		-	12	22	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =50V, V _{GS} =10V, I _{DS} =7A	-	7.5	11	nC
Q _{gs}	Gate-Source Charge		-	2.2	-	
Q _{gd}	Gate-Drain Charge		-	1.6	-	

Note d : Pulse test ; pulse width≤300μs, duty cycle≤2%.

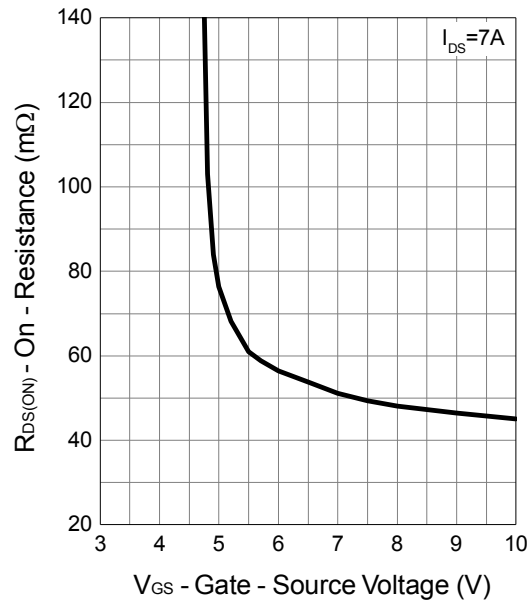
Note e : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

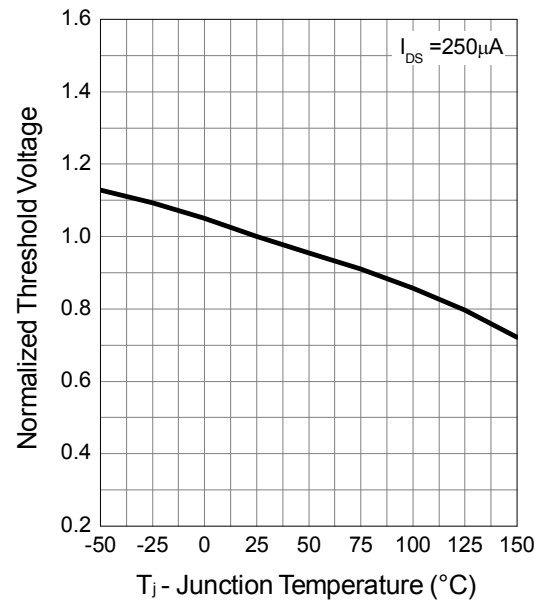


Typical Operating Characteristics (Cont.)

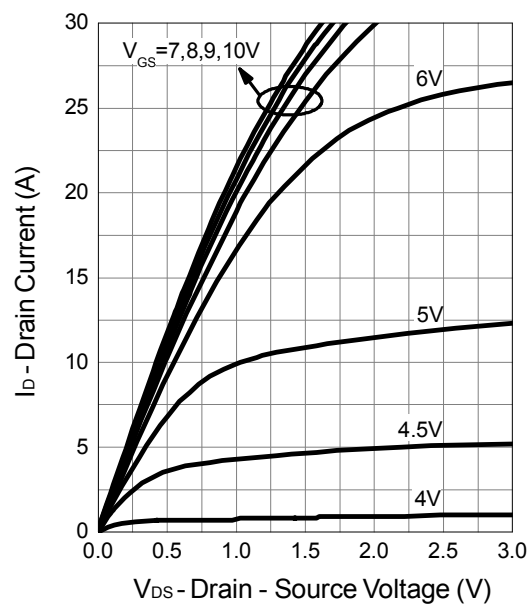
Gate-Source On Resistance



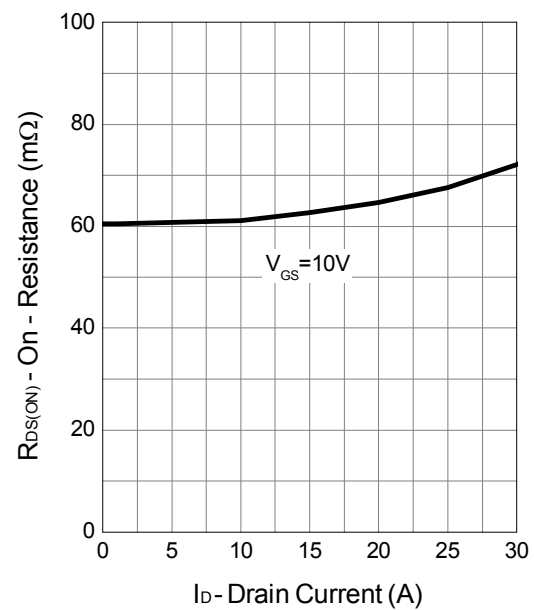
Gate Threshold Voltage



Output Characteristics

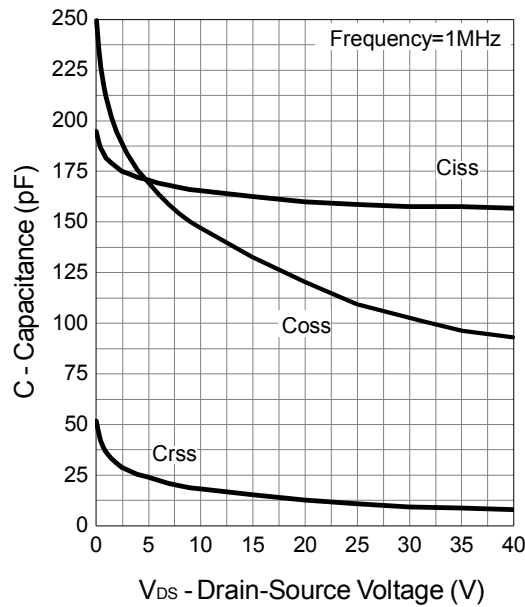


Drain-Source On Resistance

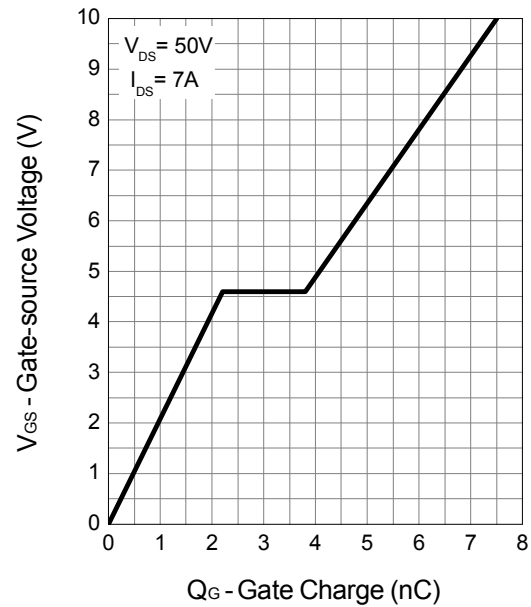


Typical Operating Characteristics (Cont.)

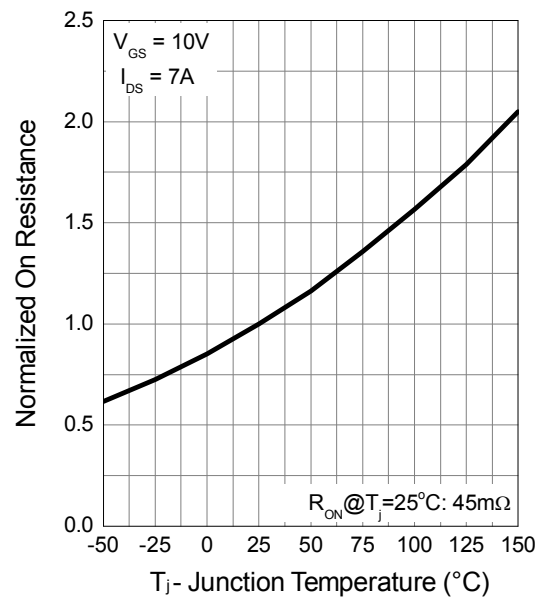
Capacitance



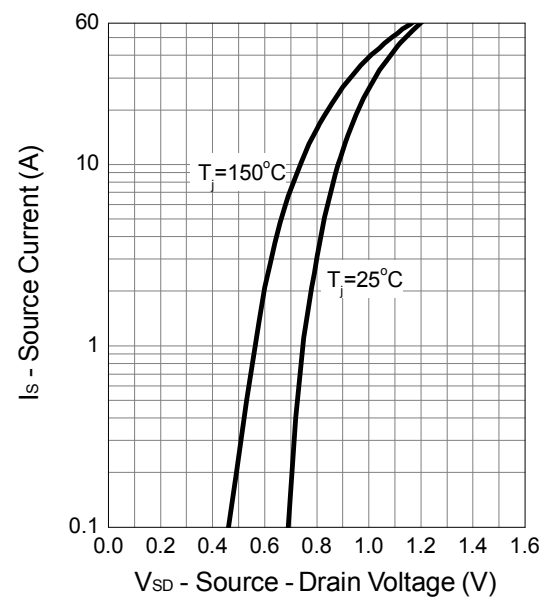
Gate Charge



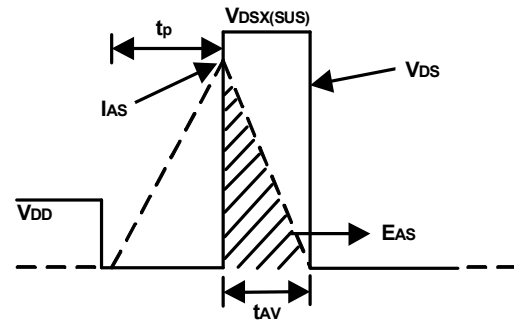
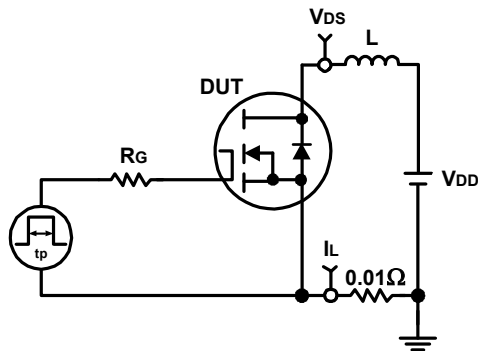
Drain-Source On Resistance



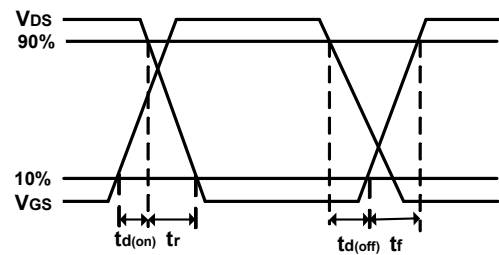
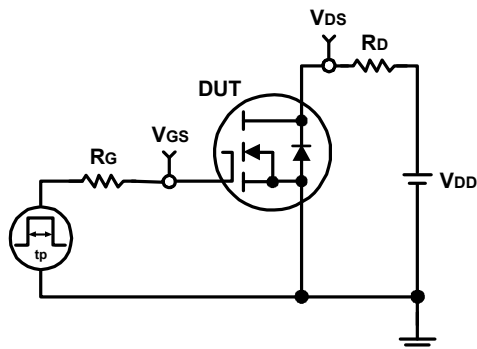
Source-Drain Diode Forward



Avalanche Test Circuit and Waveforms

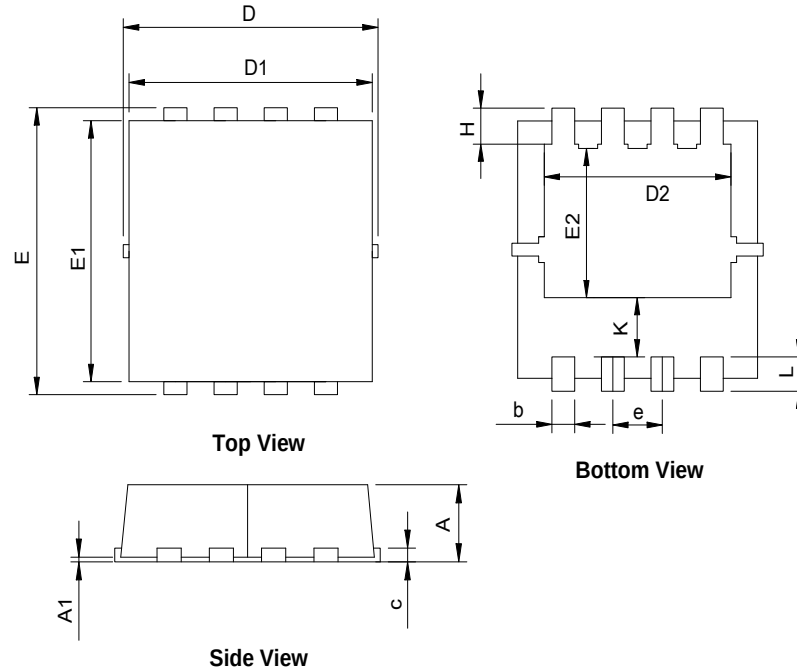


Switching Time Test Circuit and Waveforms



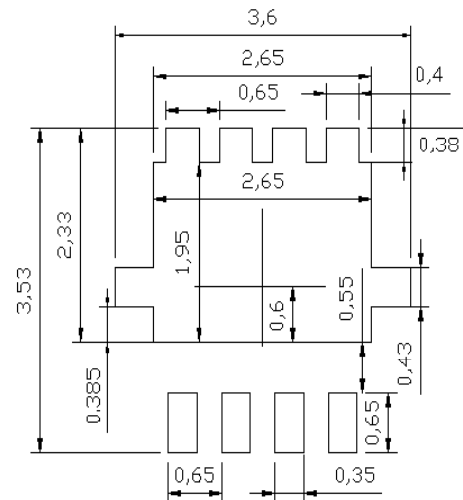
Package Information

PDFN3.3*3.3-8L



SYMBOL	PDFN3.3*3.3-8L			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.10	0.25	0.004	0.010
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.59	0.093	0.102
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.98	0.065	0.078
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022

RECOMMENDED LAND PATTERN



UNIT: mm